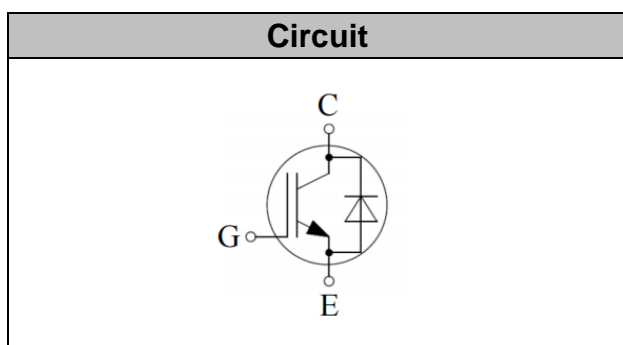


IGBT Discrete

V_{CE}	650	V
I_C	75	A
$V_{CE(SAT)} I_C=75A$	1.65	V



Applications

- High frequency switching application
- Resonant converters
- Uninterruptible power supply
- Welding converters

Features

- High speed smooth switching device for hard & soft switching
- Maximum junction temperature 175°C
- Positive temperature coefficient
- High ruggedness, temperature stable
- Pb-free lead plating; RoHS compliant

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter Breakdown Voltage	V_{CE}	650	V
DC Collector Current, limited by T_{jmax} $T_C=25^\circ C$ value limited by bondwire $T_C=100^\circ C$	I_C	85 80	A
Diode Forward Current, limited by T_{jmax} $T_C=25^\circ C$ value limited by bondwire $T_C=100^\circ C$	I_F	85 80	A
Continuous Gate-Emitter Voltage	V_{GE}	± 20	V
Transient Gate-Emitter Voltage ($t_p \leq 10\mu s, D < 0.010$)	V_{GE}	± 30	V
Turn off Safe Operating Area $V_{CE} \leq 650V$, $T_j \leq 150^\circ C$		300	A
Pulsed Collector Current, $V_{GE}=15V$, t_p limited by T_{jmax}	I_{CM}	300	A
Diode Pulsed Current, t_p limited by T_{jmax}	I_{Fpuls}	300	A
Power Dissipation, $T_j=175^\circ C, T_c=25^\circ C$	P_{tot}	395	W



Operating Junction Temperature	T_j	-40...+175	°C
Storage Temperature	T_s	-55...+150	°C
Soldering Temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	°C

Electrical Characteristics of the IGBT ($T_j = 25^\circ\text{C}$ unless otherwise specified):

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Collector-Emitter Breakdown Voltage	BV_{CES}	$V_{GE}=0V, I_C=250\mu A$	650		-	V
Gate Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=0.75mA$	4.25	5.05	5.85	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=75A$ $T_j=25^\circ\text{C}$, $T_j=125^\circ\text{C}$ $T_j=150^\circ\text{C}$	1.45	1.65 2.05 2.15	1.95	V
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE}=650V, V_{GE}=0V$ $T_j=25^\circ\text{C}$, $T_j=150^\circ\text{C}$			0.25 3.00	mA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE}=0V, V_{GE}=\pm 20V$			200	nA

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic						
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz$	-	8.15	-	nF
Reverse Transfer Capacitance	C_{res}		-	0.17	-	
Gate Charge	Q_G	$V_{CC}=300V, I_C=75A,$ $V_{GE}=-5V\sim+15V$	-	0.58	-	uC



Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T_j= 25°C						
Turn-on Delay Time	t _{d(on)}	V _{CC} =300V, I _C =75A, V _{GE} = 0V~15V, R _g =10Ω, L _s =60nH	-	75	-	ns
Rise Time	t _r		-	91	-	ns
Turn-on Energy	E _{on}		-	2.5	-	mJ
Turn-off Delay Time	t _{d(off)}		-	468	-	ns
Fall Time	t _f		-	41	-	ns
Turn-off Energy	E _{off}		-	1.3	-	mJ
Total switching energy	E _{ts}		-	3.8	-	mJ
Dynamic , at T_j= 125°C						
Turn-on Delay Time	t _{d(on)}	V _{CC} =300V, I _C =75A, V _{GE} = 0V~15V, R _g =10Ω, L _s =60nH	-	70	-	ns
Rise Time	t _r		-	79	-	ns
Turn-on Energy	E _{on}		-	3.5	-	mJ
Turn-off Delay Time	t _{d(off)}		-	508	-	ns
Fall Time	t _f		-	48	-	ns
Turn-off Energy	E _{off}		-	1.6	-	mJ
Total switching energy	E _{ts}		-	5.1	-	mJ
Dynamic , at T_j= 150°C						
Turn-on Delay Time	t _{d(on)}	V _{CC} =300V, I _C =75A, V _{GE} = 0V~15V, R _g =10Ω, L _s =60nH	-	68	-	ns
Rise Time	t _r		-	76	-	ns
Turn-on Energy	E _{on}		-	3.7	-	mJ
Turn-off Delay Time	t _{d(off)}		-	519	-	ns
Fall Time	t _f		-	52	-	ns
Turn-off Energy	E _{off}		-	1.7	-	mJ
Total switching energy	E _{ts}		-	5.4	-	mJ

**Electrical Characteristics of the Diode** ($T_j = 25^\circ\text{C}$ unless otherwise specified):

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Diode Forward Voltage	V_F	$I_F = 75\text{A}$ $T_j = 25^\circ\text{C}$, $T_j = 125^\circ\text{C}$ $T_j = 150^\circ\text{C}$	1.35	1.61 1.45 1.41	1.95	V

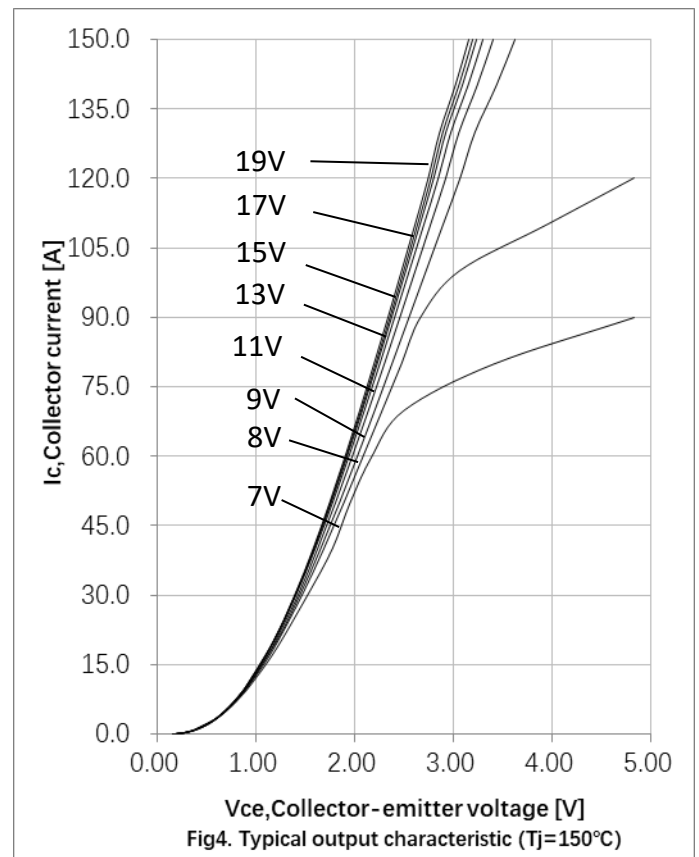
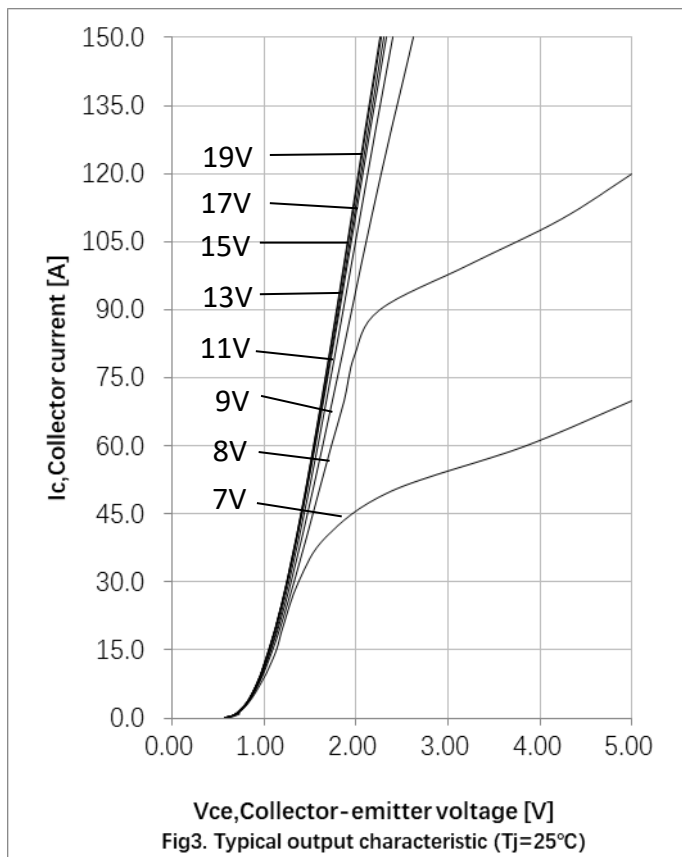
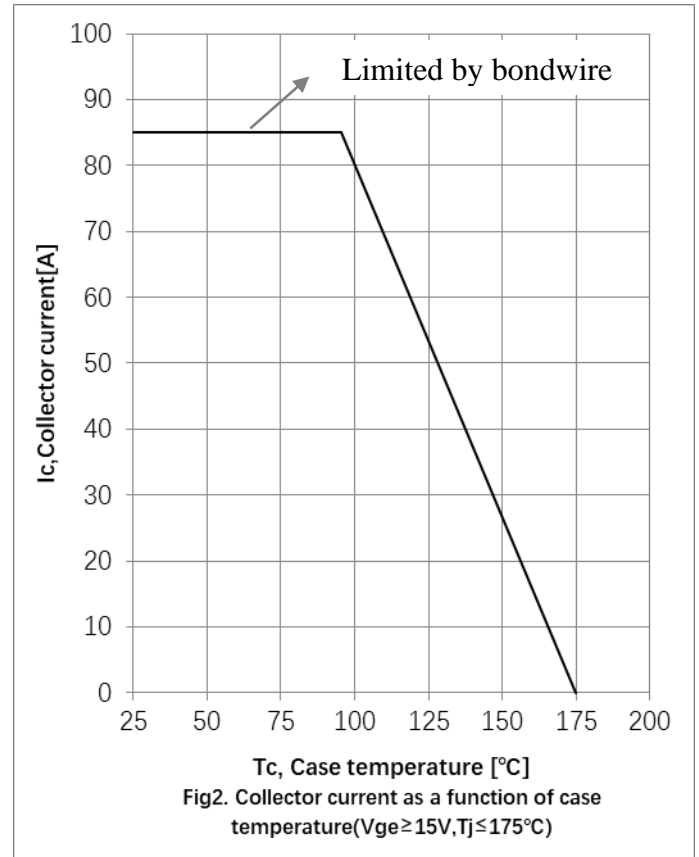
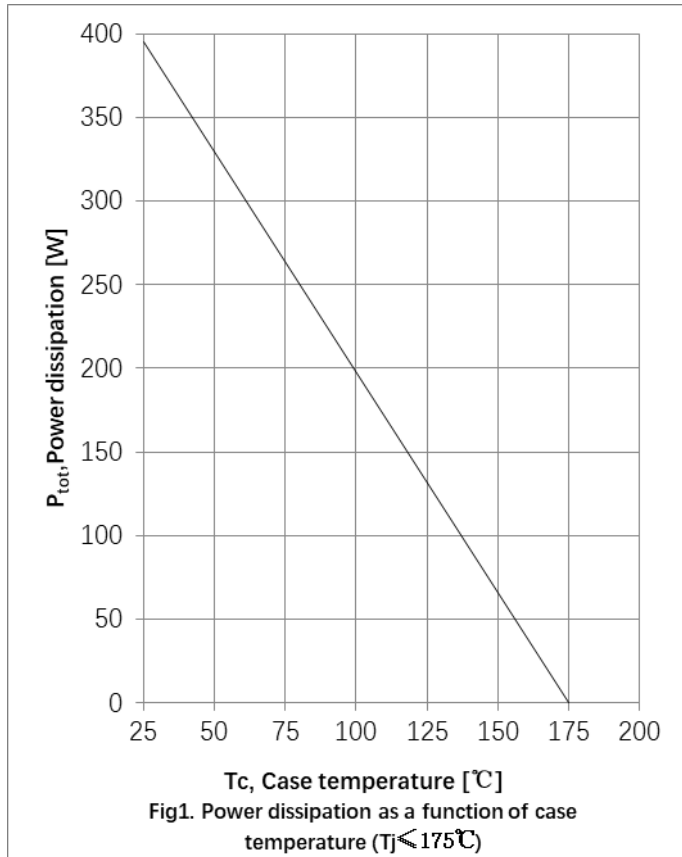
Electrical Characteristics of the DIODE

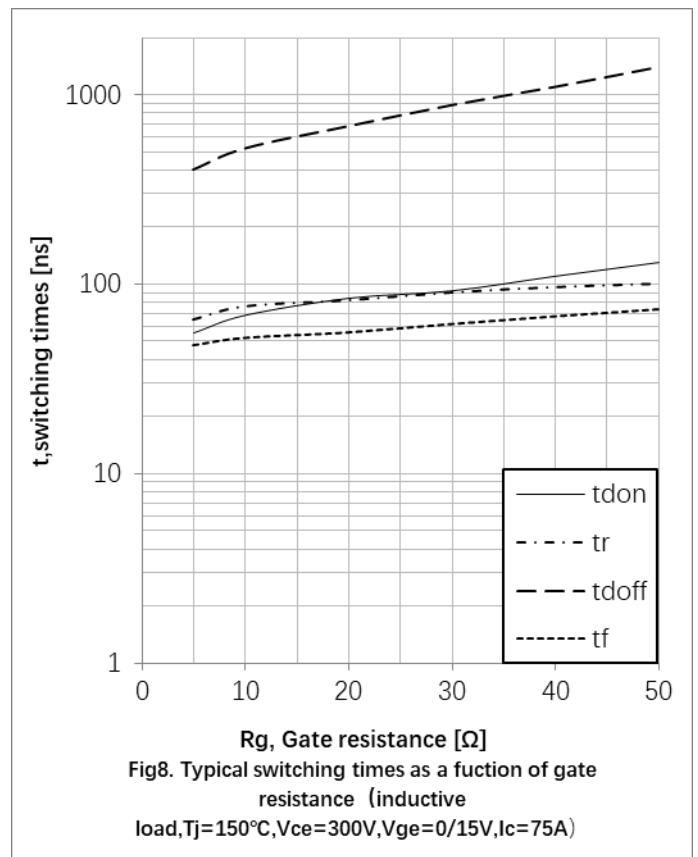
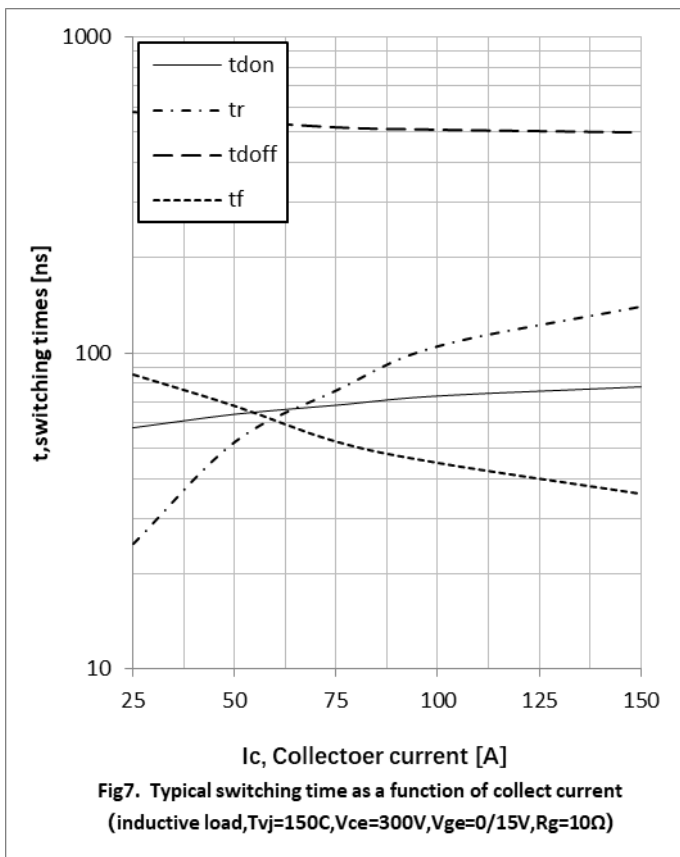
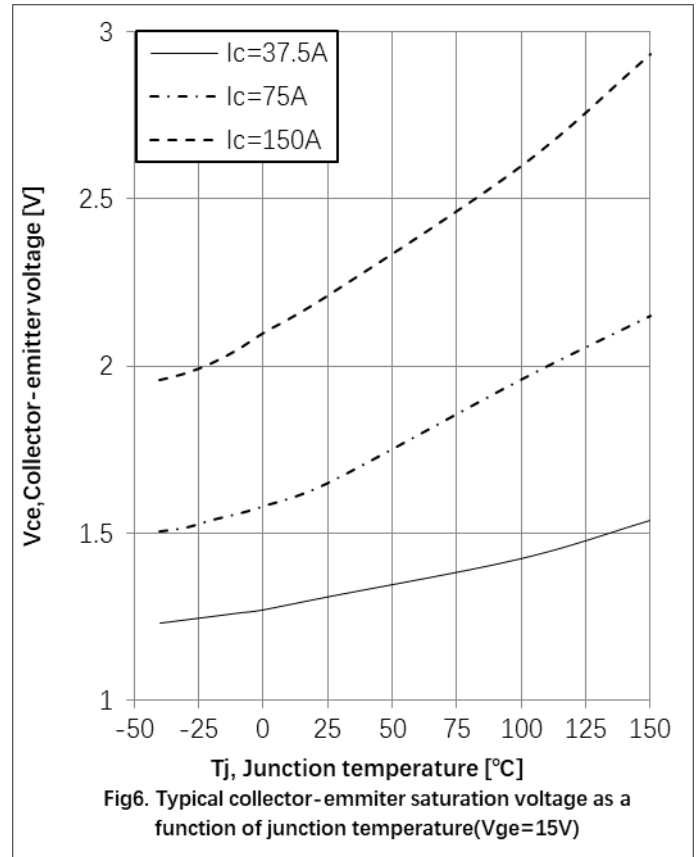
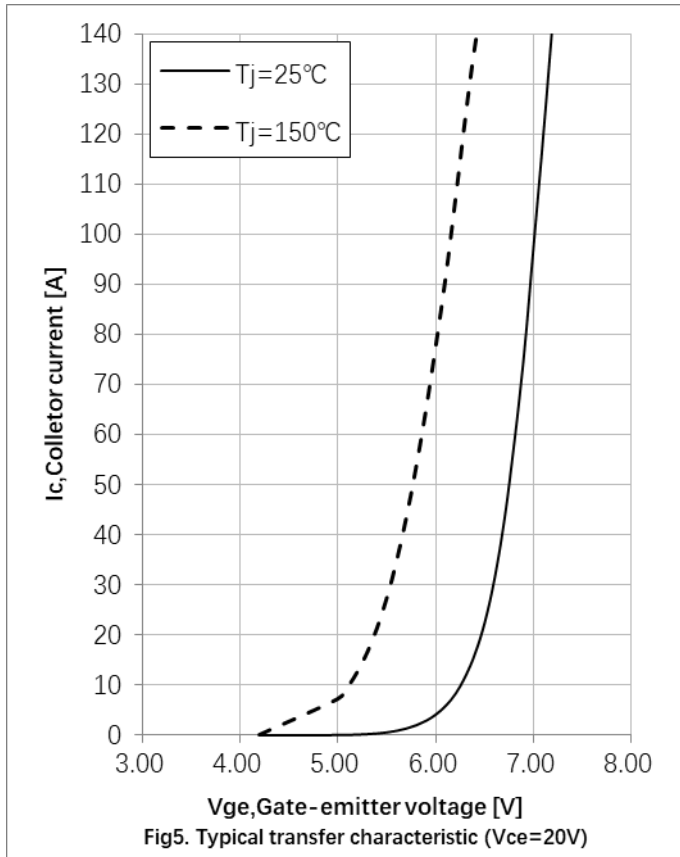
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at $T_j = 25^\circ\text{C}$						
Reverse Recovery Current	I_{rr}	$I_F = 75\text{A}, V_R = 300\text{V}$ $-di/dt = 550\text{A}/\mu\text{s}$,	-	13	-	A
Reverse Recovery Charge	Q_{rr}		-	0.73	-	μC
Diode reverse recovery time	t_{rr}		-	100	-	ns
Reverse Recovery Energy	E_{rec}		-	0.12	-	mJ
Dynamic , at $T_j = 125^\circ\text{C}$						
Reverse Recovery Current	I_{rr}	$I_F = 75\text{A}, V_R = 300\text{V}$ $-di/dt = 550\text{A}/\mu\text{s}$,	-	32	-	A
Reverse Recovery Charge	Q_{rr}		-	3.40	-	μC
Diode reverse recovery time	t_{rr}		-	140	-	ns
Reverse Recovery Energy	E_{rec}		-	0.40	-	mJ
Dynamic , at $T_j = 150^\circ\text{C}$						
Reverse Recovery Current	I_{rr}	$I_F = 75\text{A}, V_R = 300\text{V}$ $-di/dt = 550\text{A}/\mu\text{s}$,	-	38	-	A
Reverse Recovery Charge	Q_{rr}		-	3.58	-	μC
Diode reverse recovery time	t_{rr}		-	160	-	ns
Reverse Recovery Energy	E_{rec}		-	0.49	-	mJ

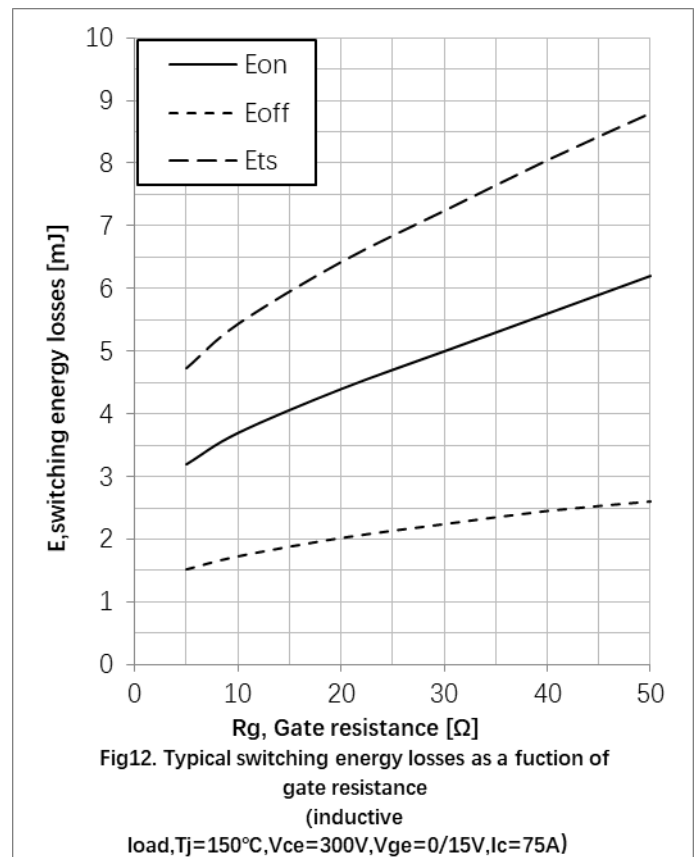
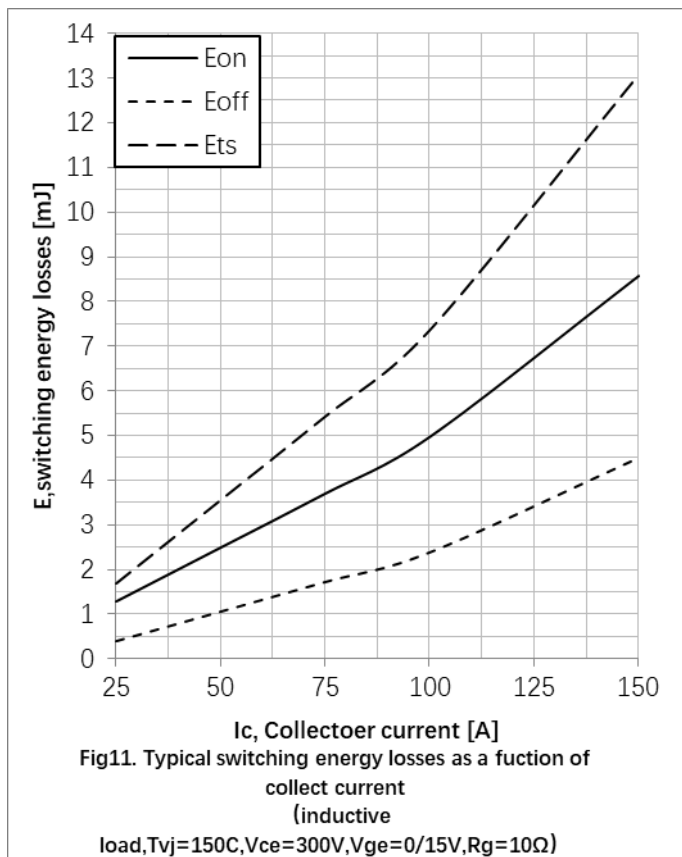
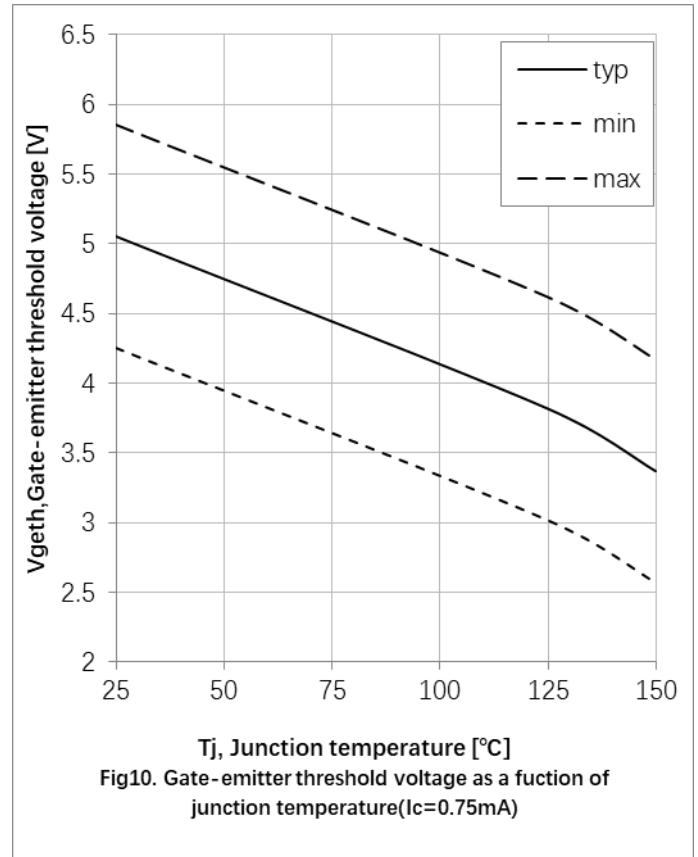
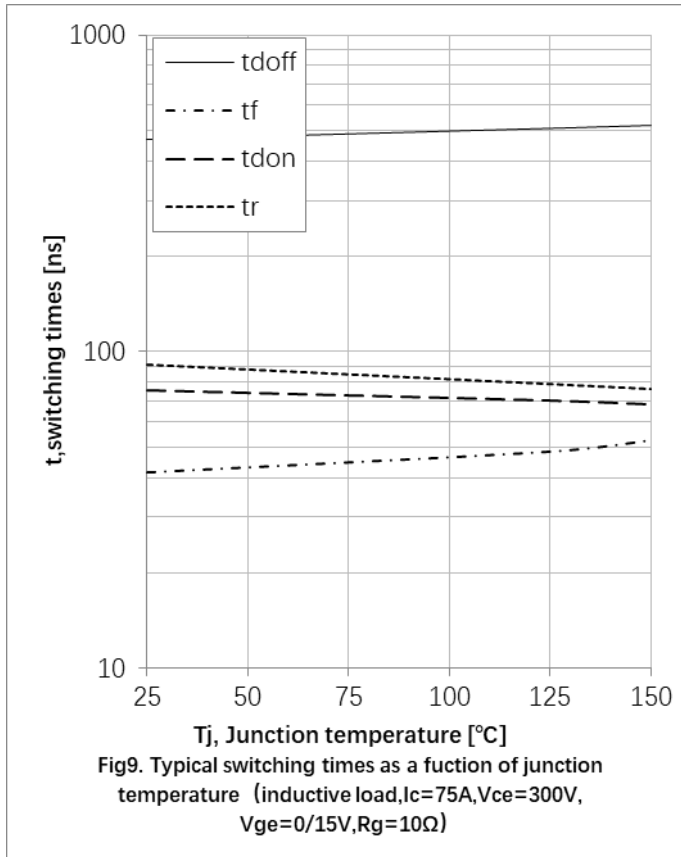


Thermal Resistance

Parameter	Symbol	Max. Value	Unit
IGBT Thermal Resistance, Junction - Case	$R_{th(j-c)}$	0.38	K/W
Diode Thermal Resistance, Junction - Case	$R_{th(j-c)}$	0.45	K/W
Thermal Resistance, Junction - Ambient	$R_{th(j-a)}$	40	K/W







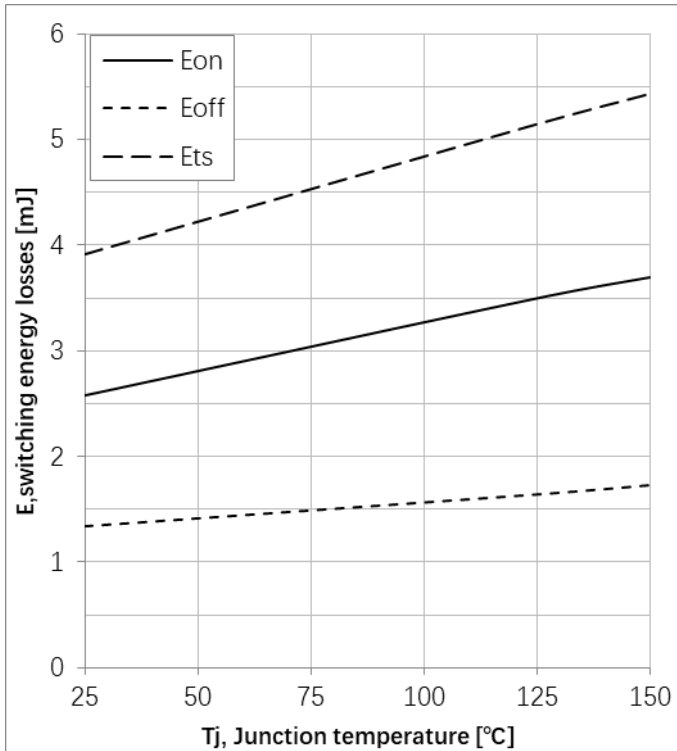


Fig13. Typical switching energy losses as a function of junction temperature (inductive load, I_c=75A, V_{ce}=300V, V_{ge}=0/15V, R_g=10Ω)

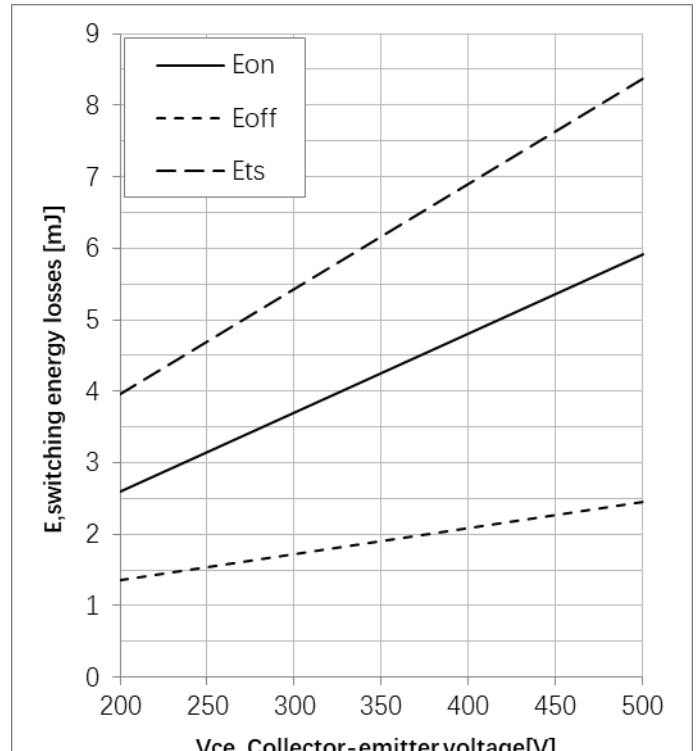


Fig14. Typical switching energy losses as a function of collector-emitter voltage (inductive load, T_j=150°C, I_c=75A, V_{ge}=0/15V, R_g=10Ω)

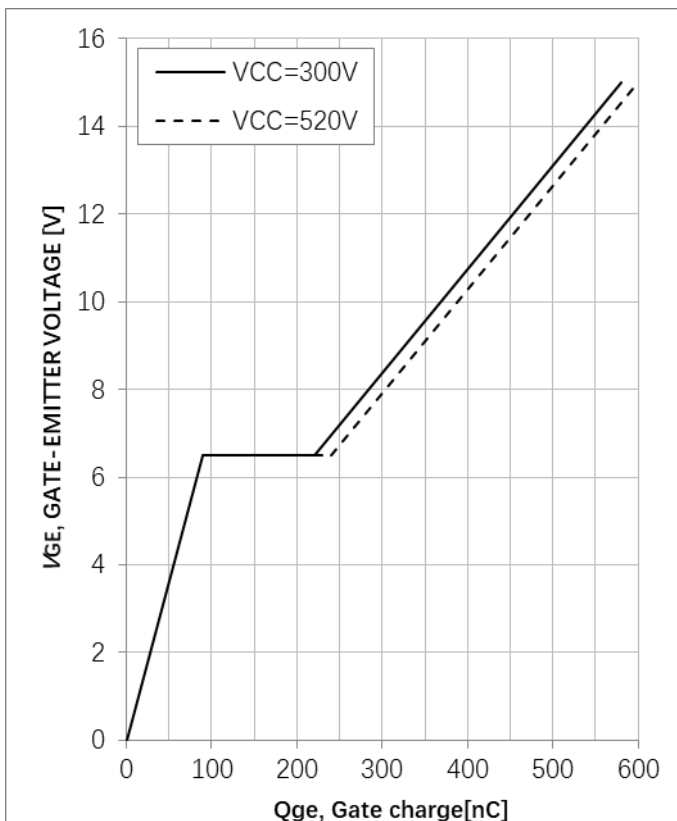


Fig15. Typical gate charge

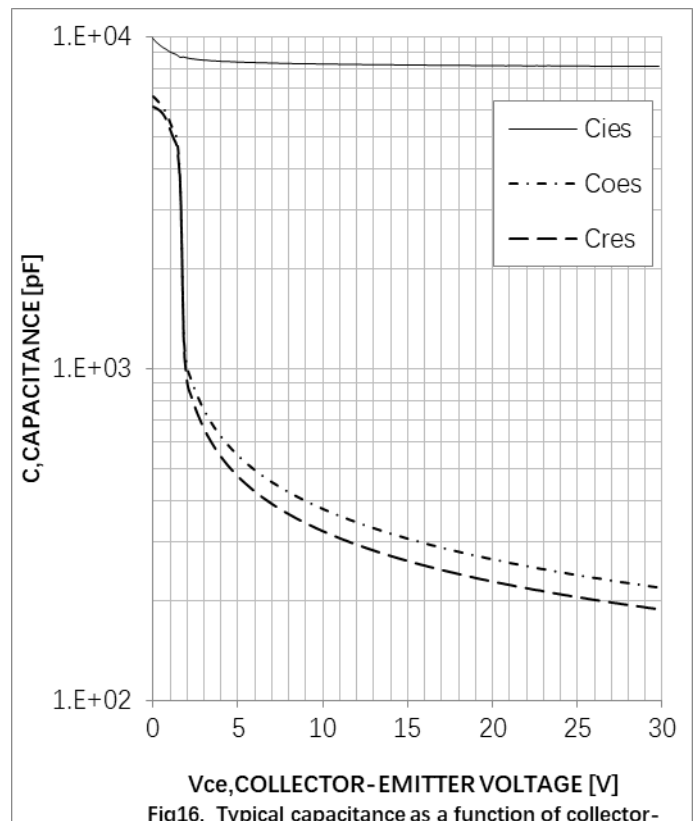
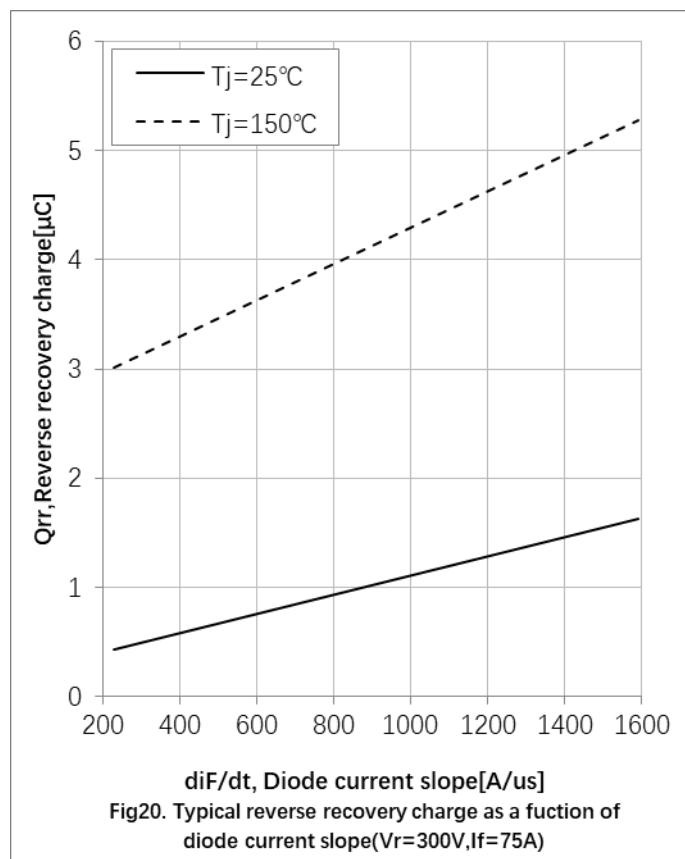
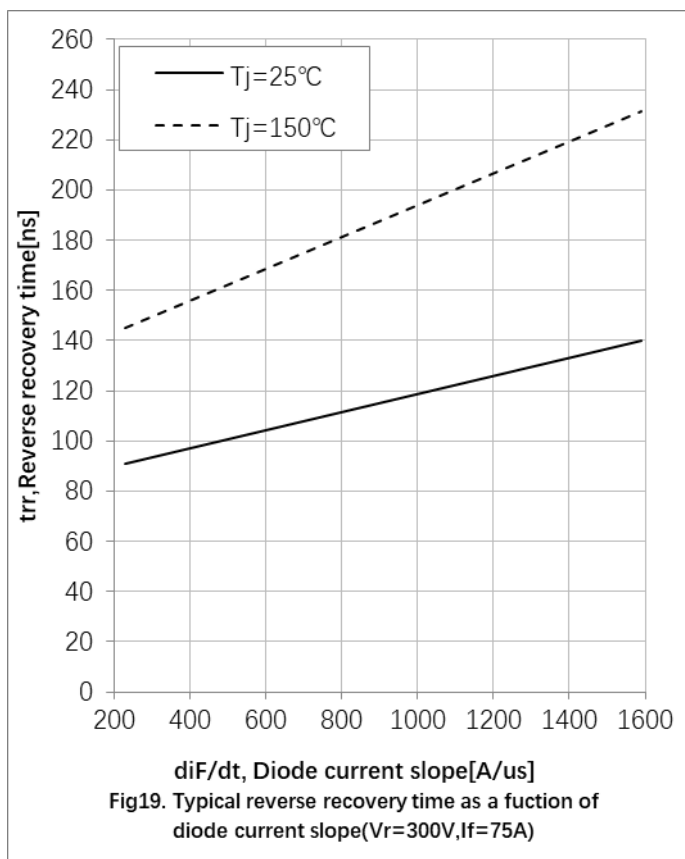
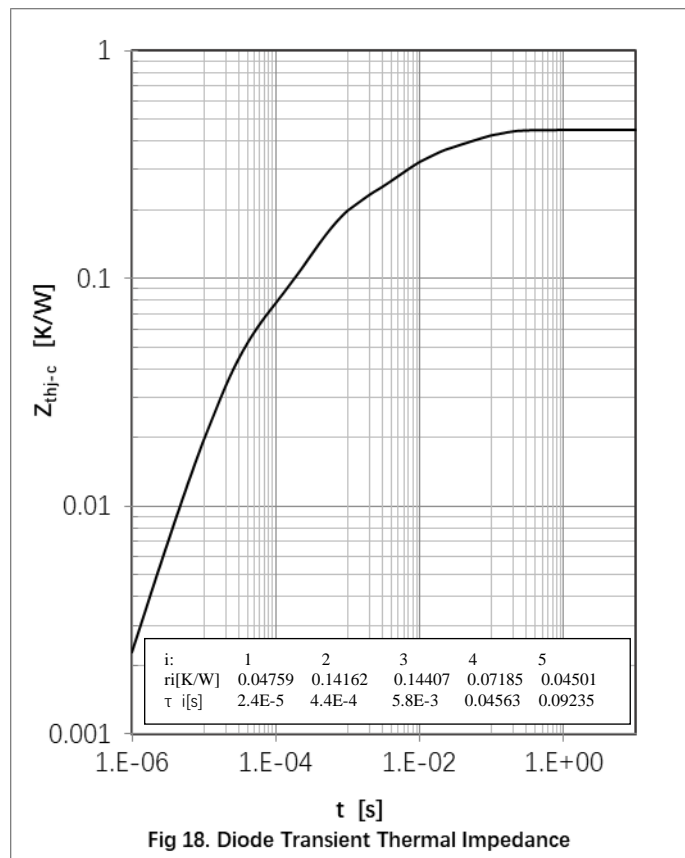
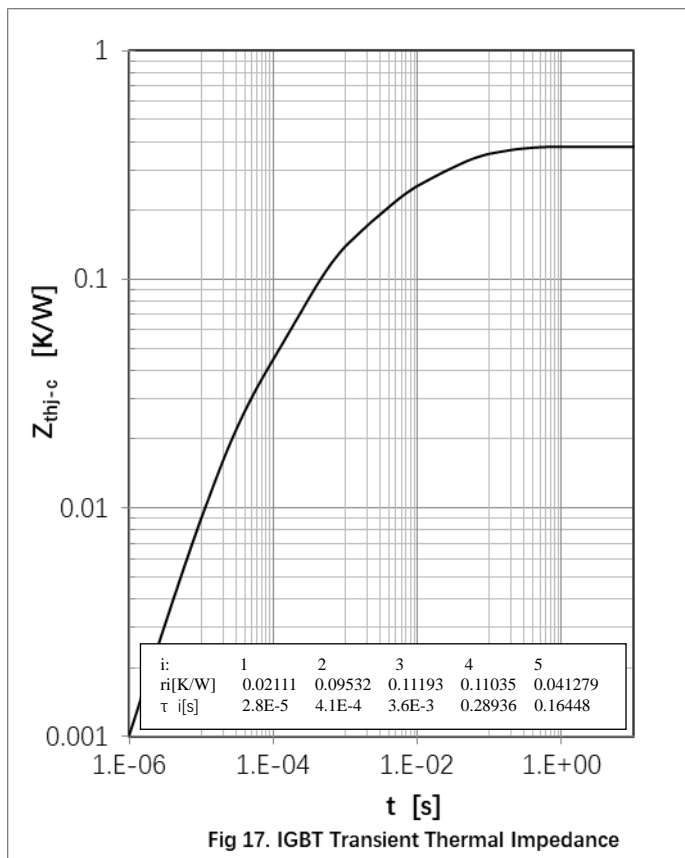
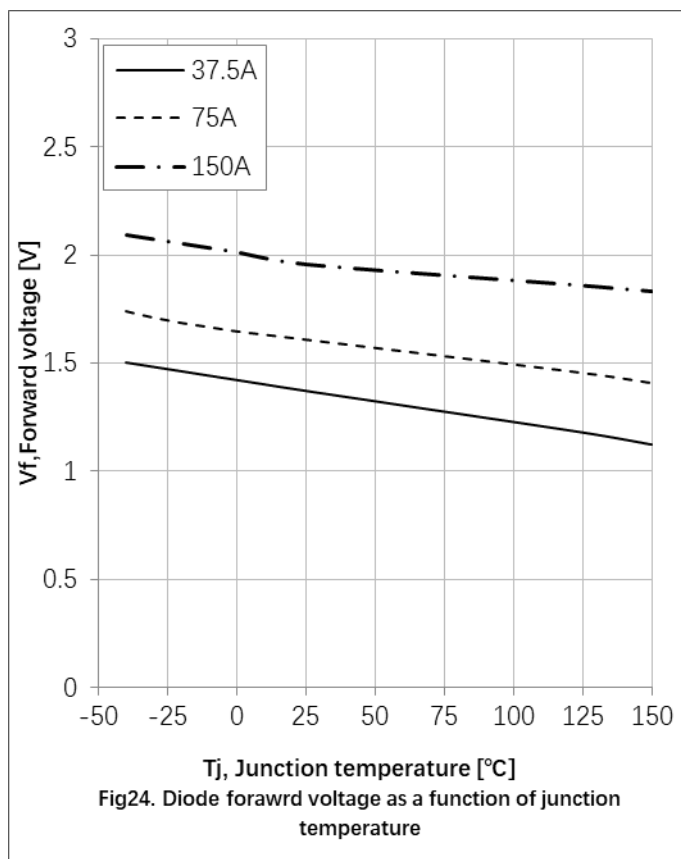
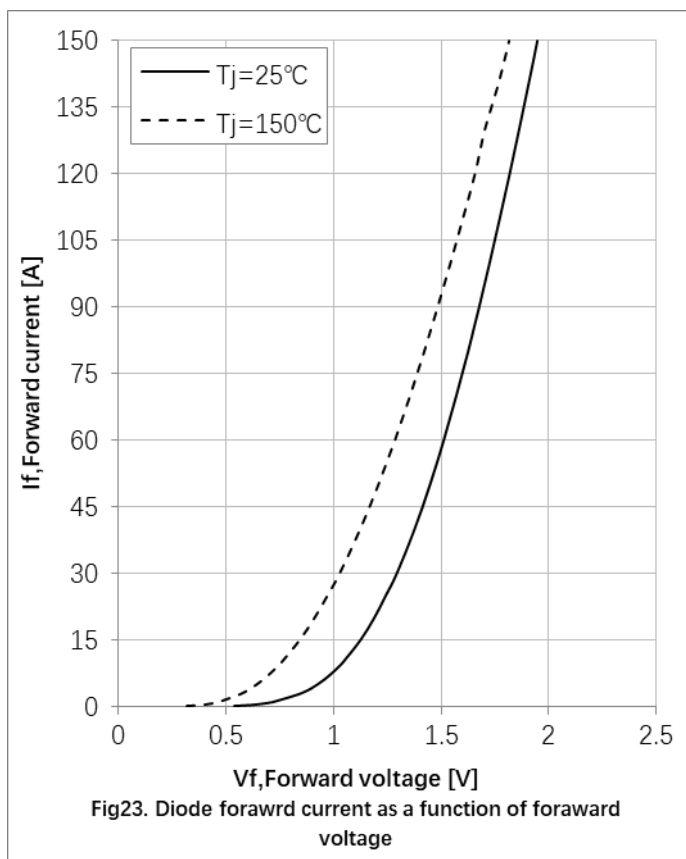
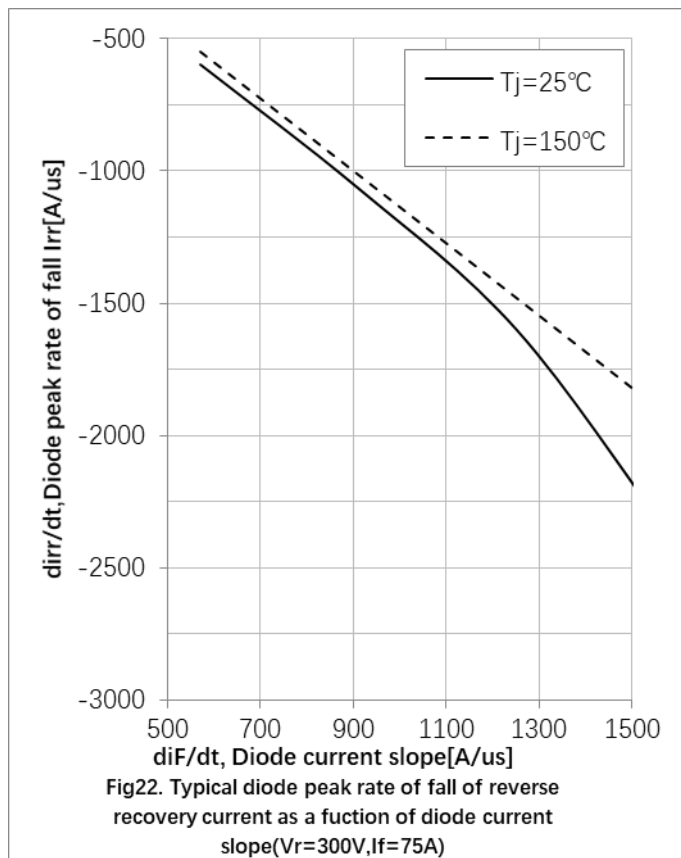
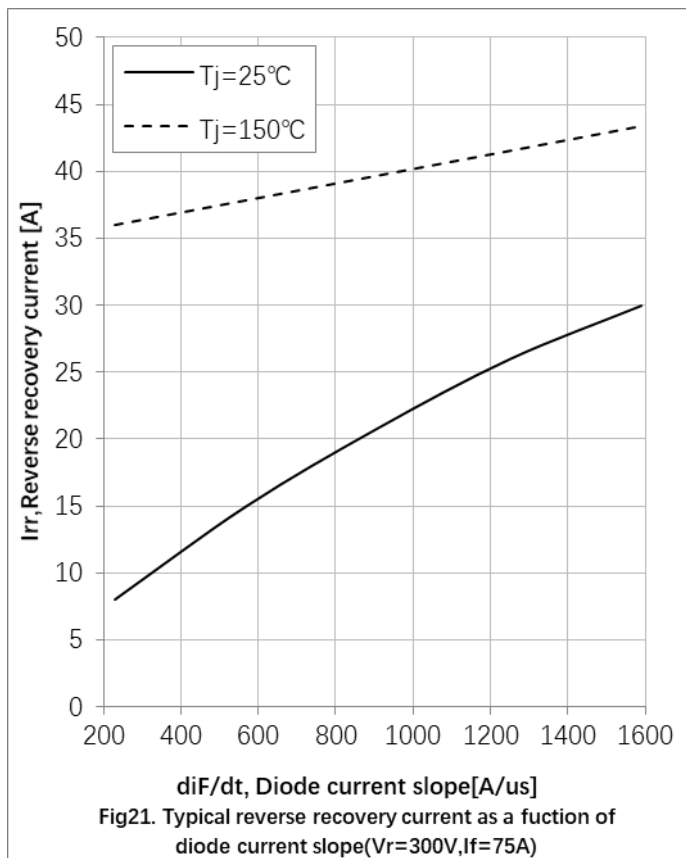
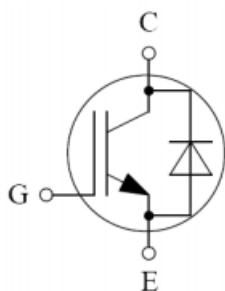


Fig16. Typical capacitance as a function of collector-emitter voltage

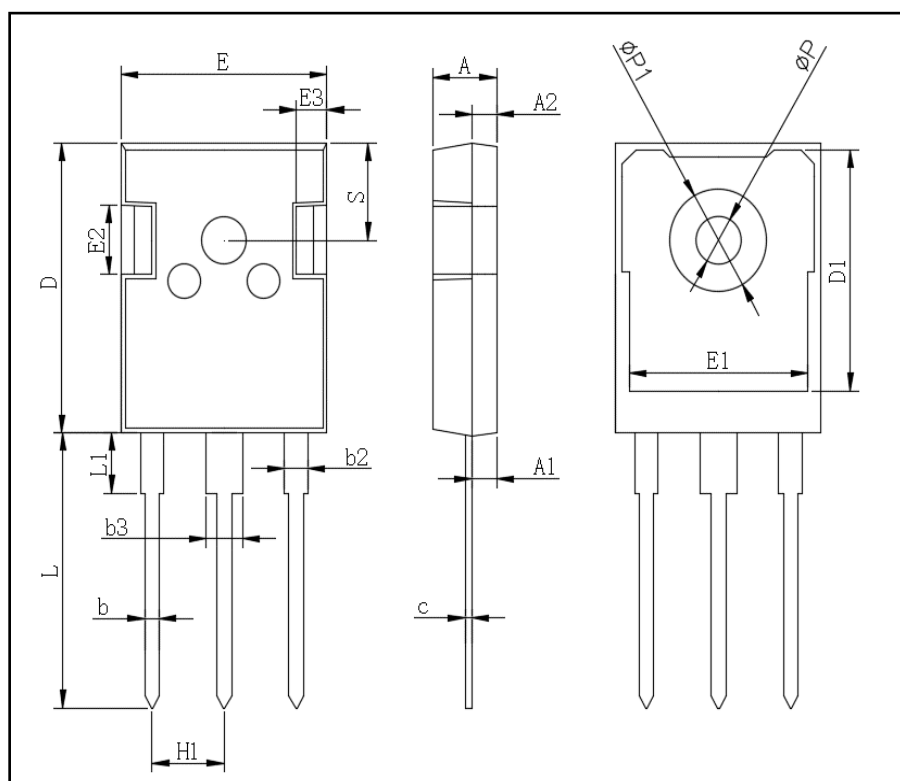




● **Circuit Diagram**



● **Package Outline Information**



TO-247AB		
Dim	Min	Max
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.0	1.4
b2	1.91	2.21
C	0.5	0.7
D	20.70	21.30
D1	16.25	16.85
E	15.50	16.10
E1	13.0	13.6
E2	4.80	5.20
E3	2.30	2.70
L	19.62	20.22
L1	-	4.30
ΦP	3.40	3.80
ΦP1	-	7.30
S	6.15TYP	
H1	5.44TYP	
b3	2.80	3.20